



SLVS397C - JULY 2001 - REVISED FEBRUARY 2005





6-A OUTPUT ACTIVE BUS TERMINATION SYNCHRONOUS PWM SWITCHER WITH INTEGRATED FETs (SWIFT™)

FEATURES

- Tracks Externally Applied Reference Voltage
- 30-m Ω , 12-A Peak MOSFET Switches for High Efficiency at 6-A Continuous Output Source or Sink Current
- 6% to 90% VIN Output Tracking Range
- **PWM Frequency Range:** Fixed 350 kHz or Adjustable 280 to 700 kHz
- Load Protected by Peak Current Limit and **Thermal Shutdown**
- Integrated Solution Reduces Board Area and **Component Count**

APPLICATIONS

- **DDR Memory Termination Voltage**
- **Active Termination of GTL and STL High-Speed Logic Families**
- **DAC Controlled High Current Output Stage**
- **Precision Point of Load Power Supply**

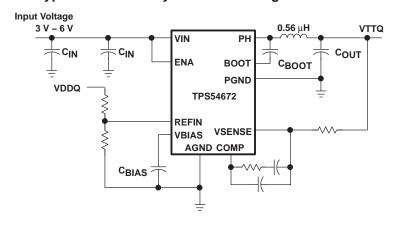
DESCRIPTION

As a member of the SWIFT™ family of dc/dc regulators, the TPS54672 active bus termination synchronous PWM converter integrates all required active components. Included on the substrate with the listed features are a true, high performance, voltage error amplifier that enables maximum performance and flexibility in choosing the output filter L and C components; an under-voltagelockout circuit to prevent start-up until the input voltage reaches 3 V; a slow-start control to limit in-rush currents; and a status output to indicate valid operating conditions.

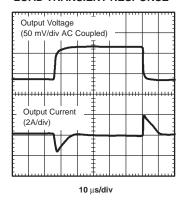
The TPS54672 is available in a thermally enhanced 28-pin TSSOP (PWP) PowerPAD™ package, which eliminates bulky heatsinks. TI provides evaluation modules and the SWIFT™ designer software tool to aid in quickly achieving high-performance power supply designs to meet aggressive equipment development cycles.

SIMPLIFIED SCHEMATIC

Typical DDR Memory Termination Regulator Circuit



LOAD TRANSIENT RESPONSE



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

| TA | T _A REFIN VOLTAGE | | PART NUMBER |
|---------------|------------------------------|-------------------------|-------------|
| -40°C to 85°C | 0.2 V to 1.75 V | Plastic HTSSOP (PWP)(1) | TPS54672PWP |

⁽¹⁾ The PWP package is also available taped and reeled. Add an R suffix to the device type (i.e., TPS54672PWPR). See the application section of the data sheet for PowerPAD™ drawing and layout information.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

| | | TPS54672 | | |
|---------------------------------------|---|--------------------|--|--|
| | VIN, ENA | -0.3 V to 7 V | | |
| Input voltage range, V _I | RT | -0.3 V to 6 V | | |
| | VSENSE, REFIN | -0.3 V to 4 V | | |
| | BOOT | −0.3 V to 17 V | | |
| 0 | VBIAS, COMP, STATUS | –0.3 V to 7 V | | |
| Output voltage range, VO | PH | -0.3 V to 10 V | | |
| | PH | Internally Limited | | |
| Source current, IO | COMP, VBIAS | 6 mA | | |
| | PH | 12 A | | |
| Sink current, IS | COMP | 6 mA | | |
| - | STATUS | 10 mA | | |
| Voltage differential, AGND to PG | ND | ±0.6 V | | |
| Operating virtual junction tempera | -40°C to 125°C | | | |
| Storage temperature, T _{Stg} | −65°C to 150°C | | | |
| Lead temperature 1,6 mm (1/16 i | ead temperature 1,6 mm (1/16 inch) from case for 10 seconds | | | |

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS(1)(2)

| PACKAGE | THERMAL IMPEDANCE JUNCTION-TO-AMBIENT | T _A = 25°C POWER RATING | T _A = 70°C POWER RATING | T _A = 85°C POWER RATING | |
|---------------------------|---------------------------------------|---------------------------------------|---------------------------------------|---------------------------------------|--|
| 28 Pin PWP with solder | 18.2 °C/W | 5.49 W(3) | 3.02 W | 2.20 W | |
| 28 Pin PWP without solder | 40.5 °C/W | 2.48 W | 1.36 W | 0.99 W | |

⁽¹⁾ For more information on the PWP package, refer to TI technical brief, literature number SLMA002.

- 1. 3" x 3", 4 layers, thickness: 0.062"
- 2. 1.5 oz. copper traces located on the top of the PCB
- 3. 1.5 oz. copper ground plane on the bottom of the PCB
- 4. 0.5 oz. copper ground planes on the 2 internal layers
- 5. 12 thermal vias (see "Recommended Land Pattern" in applications section of this data sheet)
- (3) Maximum power dissipation may be limited by over current protection.

ADDITIONAL 6A SWIFT™ DEVICES, (REFER TO SLVS398 AND SLVS400)

| DEVICE | OUTPUT VOLTAGE | DEVICE | OUTPUT VOLTAGE | DEVICE | OUTPUT VOLTAGE |
|----------|----------------|----------|----------------|----------|------------------------------|
| TPS54611 | 0.9 V | TPS54614 | 1.8 V | TPS54610 | Adjustable |
| TPS54612 | 1.2 V | TPS54615 | 2.5 V | TPS54673 | Disabled sink during startup |
| TPS54613 | 1.5 V | TPS54616 | 3.3 V | TPS54680 | Sequencing |

⁽²⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

⁽²⁾ Test board conditions:



ELECTRICAL CHARACTERISTICS

 $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_I = 3$ V to 6 V over operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------|--|--|-------|------|------|----------------|
| SUPPL | Y VOLTAGE, VIN | | | | | |
| | Input voltage range, VIN | | 3.0 | | 6.0 | V |
| VID | Differential voltage, AGND to PGND | | -0.30 | | 0.30 | V |
| | | Switching freq. = 350 kHz, RT open | | 10 | 16 | |
| l(Q) | Quiescent current | Switching freq. = 500 kHz, RT = 100 k Ω | | 16 | 24 | mA |
| (/ | | Shutdown, SS/ENA = 0 V | | 1 | 1.4 | |
| UNDE | RVOLTAGE LOCKOUT | | | | | |
| | Start threshold voltage, UVLO | | | 2.95 | 3.00 | V |
| | Stop threshold voltage, UVLO | | 2.70 | 2.80 | | V |
| | Hysteresis voltage, UVLO | | 0.14 | 0.16 | | V |
| | Rising and falling edge deglitch, UVLO(1) | | | 2.5 | | μs |
| BIAS V | OLTAGE | | | | | |
| | Output voltage, VBIAS | I _(VBIAS) = 0 | 2.70 | 2.80 | 2.90 | V |
| | Output current, VBIAS (2) | () | | | 100 | μΑ |
| CUMU | LATIVE REFERENCE | 1 | 1 | | | • |
| | Cumulative regulation accuracy (relative to REFIN) | I _O = -6A to 6A, Switching frequency = 350 kHz, REFIN = 1.25 V ⁽¹⁾ | -1.5% | | 1.5% | |
| OSCIL | LATOR | | • | | ' | |
| | Internally set—free running frequency | RT open | 280 | 350 | 420 | kHz |
| | Externally set—free running frequency range | RT = $68 \text{ k}\Omega$ to $180 \text{ k}\Omega$ | 280 | | 700 | kHz |
| | Externally set—free running frequency accuracy | RT = 100 k Ω (1% resistor to AGND) | 460 | 500 | 540 | kHz |
| | Ramp valley | | | 0.75 | | V |
| | Ramp amplitude (peak-to-peak) | | | 1 | | V |
| | Minimum controllable on time(1) | | | | 200 | ns |
| | Maximum duty cycle (1) | | 90% | | | |
| | Error amplifier open loop voltage gain | 1 kΩ COMP to AGND (1) | 90 | 110 | | dB |
| | Error amplifier unity gain bandwidth | Parallel 10 kΩ, 160 pF COMP to AGND (1) | 3 | 5 | | MHz |
| | Error amplifier common mode input voltage range(1) | | 0 | | 2.85 | V |
| | Error amplifier common mode rejection ratio(1) | | | 65 | | dB |
| | Input bias current, VSENSE | VSENSE = REFIN = 1 V | | 60 | 250 | nA |
| | Input bias current, REFIN | VSENSE = REFIN = 1.25 V | | 60 | 250 | nA |
| | Input offset voltage, REFIN | VSENSE = REFIN = 1.25 V | -1.5 | | 1.5 | mV |
| | Input voltage range, REFIN ⁽¹⁾ | | 0 | | 1.8 | V |
| | Output voltage slew rate (symmetric), COMP | | 1 | 1.4 | | V/μs |
| | , | I _O = 3 mA | · · | •••• | 2.65 | |
| | Common mode output voltage range, COMP | $I_O = -3 \text{ mA}$ | 0.2 | | | V |
| | PWM comparator propagation delay time, PWM comparator input to PH pin (excluding deadtime) | 10-mV overdrive (1) | | 70 | 85 | ns |
| | Enable threshold voltage, ENA | | 0.82 | 1.20 | 1.40 | V |
| | Enable hysteresis voltage, ENA (1) | | | 0.03 | | V |
| | Falling edge deglitch, ENA (1) | | İ | 2.5 | | μs |
| | Leakage current, ENA | V _I = 5.5 V | | | 1 | <u>.</u> μΑ |

⁽¹⁾ Ensured by design (2) Static resistive loads only



ELECTRICAL CHARACTERISTICS Continued

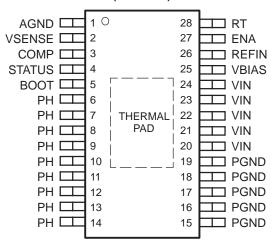
 $T_J = -40^{\circ}C$ to $+125^{\circ}C$, $V_I = 3$ V to 6 V over operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------|--------------------------------|------------------------------|-----|------|-----|------|
| OSCILLATOR (COM | ITINUED) | · | • | | | |
| Output sa | turation voltage, STATUS | I _(sink) = 2.5 mA | | 0.18 | 0.3 | V |
| Leakage o | current, STATUS | V _I = 5.5 V | | | 1 | μΑ |
| Current limit trip point | | VIN = 3 V (1) | 7 | 10 | | Δ. |
| Current iir | nit trip point | VIN = 6 V (1) | 10 | 12 | | Α |
| Current lin | nit leading edge blanking time | | | 100 | | ns |
| Current lin | nit total response time | | | 200 | | ns |
| Thermal s | hutdown trip point (1) | | 135 | 150 | 165 | °C |
| Thermal s | hutdown hysteresis (1) | | | 10 | | °C |
| | -: NI MOCEET | $I_O = 6A, V_I = 3 V (3)$ | | 36 | 65 | 0 |
| rDS(on) Low/high- | side N-MOSFET | $I_O = 6A, V_I = 6 V (3)$ | | 26 | 47 | mΩ |

⁽¹⁾ Ensured by design

PIN ASSIGNMENTS

PWP PACKAGE (TOP VIEW)



⁽²⁾ Static resistive loads only

⁽³⁾ Matched MOSFETs, low side $r_{DS(on)}$ production tested, high side $r_{DS(on)}$ ensured by design

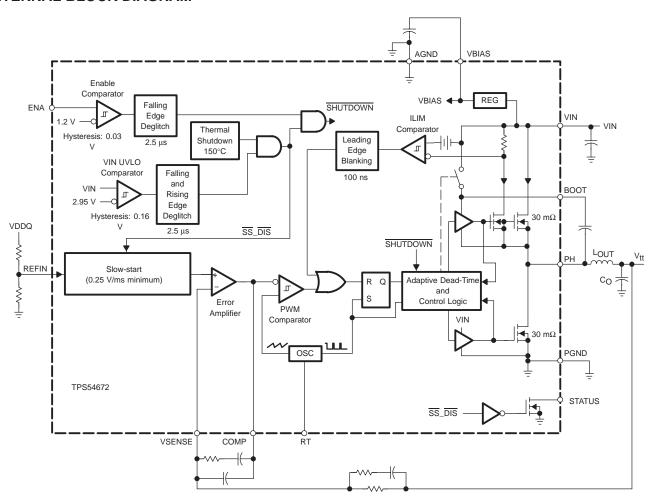


TERMINAL FUNCTIONS

| TERMINAL | | PERCENTION | | | | | | | |
|----------|-------|---|--|--|--|--|--|--|--|
| NAME | NO. | DESCRIPTION | | | | | | | |
| AGND | 1 | Analog ground. Return for compensation network/output divider, VBIAS capacitor, and RT resistor. Connect PowerPAD to AGND. | | | | | | | |
| воот | 5 | Bootstrap output. 0.022 μ F to 0.1 μ F low-ESR capacitor connected from BOOT to PH generates floating drive for the high-side FET driver. | | | | | | | |
| COMP | 3 | Error amplifier output. Connect frequency compensation network from COMP to VSENSE | | | | | | | |
| ENA | 27 | Enable input. Logic high enables oscillator, PWM control and MOSFET driver circuits. Logic low disables operation and places device in low quiescent current state. | | | | | | | |
| PGND | 15–19 | Power ground. High current return for the low-side driver and power MOSFET. Connect PGND with large copper areas to the input and output supply returns, and negative terminals of the input and output capacitors. A single point connection to AGND is recommended. | | | | | | | |
| PH | 6–14 | Phase output. Junction of the internal high-side and low-side power MOSFETs, and output inductor. | | | | | | | |
| REFIN | 26 | External reference input. High impedance input to slow-start and error amplifier circuits. | | | | | | | |
| RT | 28 | Frequency setting resistor input. Connect a resistor from RT to AGND to set the switching frequency. | | | | | | | |
| STATUS | 4 | Open drain output. Asserted low when VIN < UVLO threshold, VBIAS and internal reference are not settled or thermal shutdown active. Otherwise STATUS is high. | | | | | | | |
| VBIAS | 25 | Internal bias regulator output. Supplies regulated voltage to internal circuitry. Bypass VBIAS pin to AGND pin with a high-quality, low-ESR 0.1 - μ F to 1.0 - μ F ceramic capacitor. | | | | | | | |
| VIN | 20–24 | Input supply for the power MOSFET switches and internal bias regulator. Bypass VIN pins to PGND pins close to device package with a high-quality, low-ESR 10- μ F ceramic capacitor. | | | | | | | |
| VSENSE | 2 | Error amplifier inverting input. Connect to output voltage through compensation network/output divider. | | | | | | | |



INTERNAL BLOCK DIAGRAM

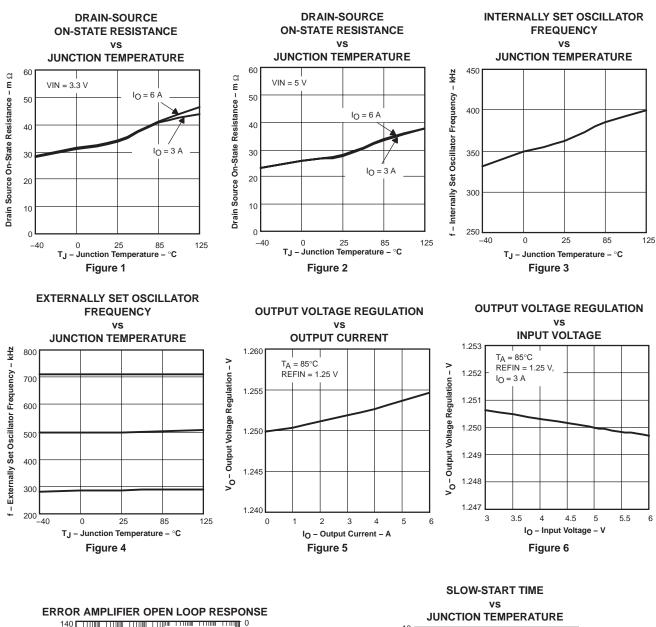


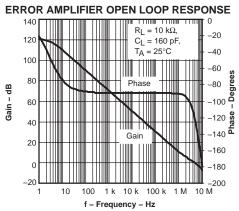
RELATED DC/DC PRODUCTS

- TPS54372
- TPS54972
- TPS54872

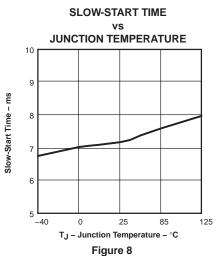


TYPICAL CHARACTERISTICS











APPLICATION INFORMATION

Figure 9 shows the schematic diagram for a typical DDR memory or GTL bus termination application using the TPS54672. The TPS54672 (U1) can provide greater than 6 A of output current. For proper operation, the exposed thermal PowerPAD underneath the integrated circuit package needs to be soldered to the printed-circuit board.

COMPONENT SELECTION

The values for the components used in this design example were selected for best load transient and tracking response. Additional design information is available at www.ti.com.

INPUT VOLTAGE

The input voltage range is 3 to 5.5 VDC. The input filter (C4) is a 10- μ F ceramic capacitor (Taiyo Yuden). C8, also a 10- μ F ceramic capacitor (Taiyo Yuden) that provides high frequency decoupling of the TPS54672 from the input supply, must be located as close as possible to the device. Ripple current is carried in both C8 and C4, and the return path to PGND should avoid the current circulating in the output capacitors C7 and C10.

FEEDBACK CIRCUIT

R1, R2, R3, C1, C2 and C3 form the loop compensation network for the circuit. For this design, a Type 3 topology is used. The compensation network, along with the output filter inductor and capacitor delivers a crossover frequency of 135 kHz with 50° of phase margin.

OPERATING FREQUENCY

In the application circuit, RT is grounded through a 71.5-k Ω resistor to select the maximum frequency of 700 kHz. To set a different frequency, place a 68-k Ω to 180-k Ω resistor between RT (pin 28) and analog ground or leave RT floating to select the default 350 kHz. The resistance can be calculated using the following equation:

$$R = \frac{500 \text{ kHz}}{\text{SwitchingFrequency}} \times 100 \text{ [k}\Omega\text{]}$$
 (1)

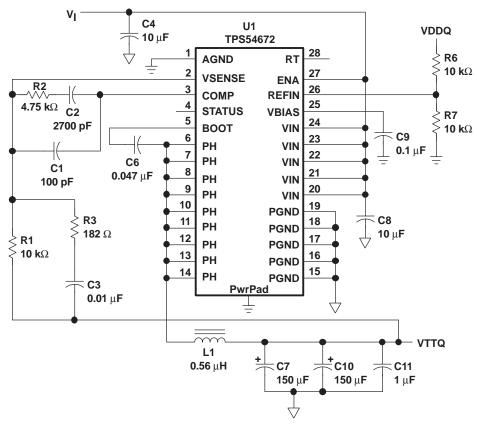


Figure 9. Application Circuit Optimized For Size And Performance



OUTPUT FILTER

The output filter is composed of a 0.56- μ H Coilcraft inductor (D01813P–561HC) and two 150- μ F Cornell Dublier capacitors (ESRD151M06R). The inductor is a low dc resistance type. The capacitors used are 4 V POSCAP types with a maximum ESR of 0.040 Ω .

PCB LAYOUT

Figure 10 shows a generalized PCB layout guide for the TPS54672. The VIN pins should be connected together on the printed circuit board (PCB) and bypassed with a low ESR ceramic bypass capacitor. Minimize the loop area formed by the bypass capacitor connections, the VIN pins, and the TPS54672 ground pins. The minimum recommended bypass capacitance is 10 μF ceramic with a X5R or X7R dielectric and the optimum placement is closest to the VIN pins and the PGND pins.

The TPS54672 has two internal grounds (analog and power). Inside the TPS54672 the analog ground ties to all of the noise sensitive signals, while the power ground ties to the noisier power signals. Noise injected between the two grounds can degrade the performance of the TPS54672, particularly at higher output currents. Ground noise on an analog ground plane can also cause problems with some of the control and bias signals. For these reasons, separate analog and power ground traces are recommended. There should be an area of ground on the top layer under the IC, with an exposed area for connection to the PowerPAD. Use vias to connect this ground area to any internal ground planes. Use additional vias at the ground side of the input and output filter capacitors as well.

The AGND and PGND pins should be tied to the PCB ground by connecting them to the ground area under the device as shown. The only components that should tie directly to the power ground plane are the input capacitors, the output capacitors, the input voltage decoupling capacitor, and the PGND pins of the TPS54672. Use a separate wide trace for the analog ground signal path. This analog ground should be used for the voltage set point divider, timing resistor RT, and bias capacitor grounds. Connect this trace directly to AGND (pin 1).

The PH pins should be tied together and routed to the output inductor. Since the PH connection is the switching node, the inductor should be located very close to the PH pins and the area of the PCB conductor minimized to prevent excessive capacitive coupling.

Connect the boot capacitor between the phase node and the BOOT pin as shown. Keep the boot capacitor close to the IC and minimize the conductor trace lengths.

Connect the output filter capacitor(s) as shown between the VOUT trace and PGND. It is important to keep the loop formed by the PH pins, Lout, Cout, and PGND as small as practical.

Place the compensation components from the VOUT trace to the VSENSE, and COMP pins. Do not place these components too close to the PH trace. Due to the size of the IC package and the device pin out, the components must be routed somewhat close, however maintaining as much separation as possible while still keeping the layout compact.

Connect the bias capacitor from the VBIAS pin to analog ground using the isolated analog ground trace. If an RT resistor is used, connect it to this trace as well.



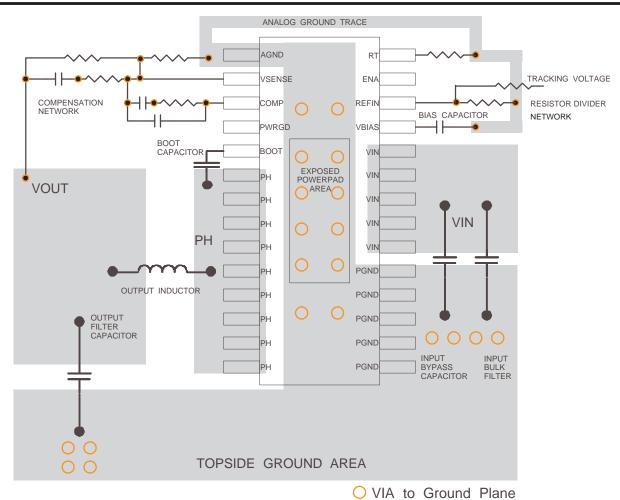


Figure 10. TPS54672 PCB Layout



LAYOUT CONSIDERATIONS FOR THERMAL PERFORMANCE

For operation at full rated load current, the analog ground plane must provide adequate heat dissipating area. A 3 inch by 3 inch plane of 1 ounce copper is recommended, though not mandatory, depending on ambient temperature and airflow. Most applications have larger areas of internal ground plane available, and the PowerPAD should be connected to the largest area available. Additional areas on the top or bottom layers also help dissipate heat, and

any area available should be used when 6 A or greater operation is desired. Connection from the exposed area of the PowerPAD to the analog ground plane layer should be made using 0.013 inch diameter vias to avoid solder wicking through the vias. Eight vias should be in the PowerPAD area with four additional vias located under the device package. The size of the vias under the package, but not in the exposed thermal pad area, can be increased to 0.018. Additional vias beyond the twelve recommended that enhance thermal performance should be included in areas not under the device package.

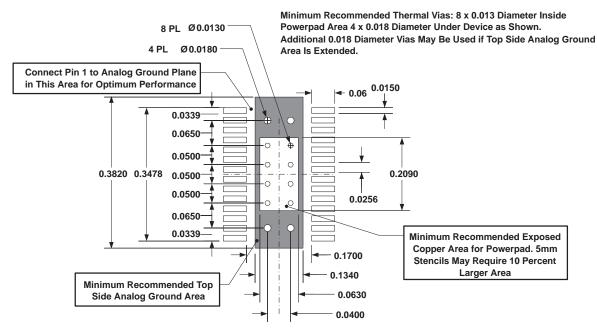


Figure 11. Recommended Land Pattern for 28-Pin PWP PowerPAD

Output Voltage (50 mV/div AC Coupled) Output Current (2A/div)

Figure 12

DETAILED DESCRIPTION

Under Voltage Lock Out (UVLO)

The TPS54672 incorporates an under voltage lockout circuit to keep the device disabled when the input voltage (VIN) is insufficient. During power up, internal circuits are

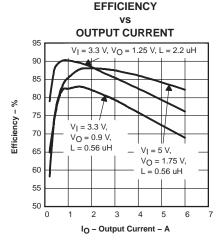


Figure 13

held inactive until VIN exceeds the nominal UVLO threshold voltage of 2.95 V. Once the UVLO start threshold is reached, device start-up begins. The device operates until VIN falls below the nominal UVLO stop threshold of



2.8 V. Note that hysteresis in the UVLO comparator and a 2.5-μs rising and falling edge deglitch circuit reduce the likelihood of shutting the device down due to noise on VIN.

Enable (ENA)

The enable pin, ENA, provides a digital control to enable or disable (shutdown) the TPS54672. An input voltage of 1.4 V or greater ensures that the TPS54672 is enabled. An input of 0.82 V or less ensures that device operation is disabled. These are not standard logic thresholds, even though they are compatible with TTL outputs.

When ENA is low, the oscillator, slow-start, PWM control and MOSFET drivers are disabled and held in an initial state ready for device start-up. On an ENA transition from low to high, device start-up begins with the output starting from 0 V.

Slow-Start

The slow-start circuit provides start-up slope control of the output voltage to limit in-rush currents. The nominal internal slow-start rate is 0.25 V/ms with the maximum rate being 0.35 V/ms. When the voltage on REFIN rises faster than the internal slope or is present when device operation is enabled, the output rises at the internal rate. If the reference voltage on REFIN rises more slowly, then the output rises at about the same rate as REFIN.

VBIAS Regulator (VBIAS)

The VBIAS regulator provides internal analog and digital blocks with a stable supply voltage over variations in junction temperature and input voltage. A high quality, low-ESR, ceramic bypass capacitor is required on the VBIAS pin. X7R or X5R grade dielectrics are recommended because their values are more stable over temperature. The bypass capacitor should be placed close to the VBIAS pin and returned to AGND.

External loading on VBIAS is allowed, with the caution that internal circuits require a minimum VBIAS of 2.7 V, and that loads with ac or digital switching noise may degrade performance. The VBIAS pin may be useful as a reference voltage for external circuits.

Oscillator Frequency (RT)

The oscillator frequency can be set to an internally fixed value of 350 kHz by leaving the RT pin unconnected (floating). If a different frequency of operation is required for the application, the oscillator frequency can be externally adjusted from 280 kHz to 700 kHz by connecting a resistor to the RT pin to ground. The operating frequency is approximated by the following equation, where R is the resistance from RT to AGND:

Switching Frequency =
$$\frac{100 \text{ k}\Omega}{\text{R}} \times 500 \text{ [kHz]}$$
 (2)

The following table summarizes the frequency selection configurations:

| FREE RUNNING FREQUENCY | RT PIN |
|-----------------------------------|-------------------|
| 350 kHz, internally set | Float |
| Externally set 280 kHz to 700 kHz | R = 68 k to 180 k |

Error Amplifier (REFIN, VSENSE, COMP)

The high performance voltage error amplifier, with wide 5MHz bandwidth, low 1.5 mV-max offset, 1.4 V/ μ s slew rate, and ground rail input range differentiates the TPS54672 from most dc/dc converters. The user is given the flexibility to use a wide range of output L and C filter components to suit the particular application needs. Type 2 or type 3 compensation can be employed using external compensation components.

The REFIN input range includes ground which allows 0% duty cycle during transient conditions. The user should note that steady state regulation accuracy of voltages less than 0.84 V is limited by the minimum controllable ON time.

PWM Control

Signals from the error amplifier output, oscillator and current limit circuit are processed by the PWM control logic. Referring to the internal block diagram, the control logic includes the PWM comparator, OR gate, PWM latch and portions of the adaptive dead time and control logic block. During steady state operation below the current limit threshold, the PWM comparator output and oscillator pulse train alternately reset and set the PWM latch. Once the PWM latch is set, the low-side FET remains on for a minimum duration set by the oscillator pulse width. During this period, the PWM ramp discharges rapidly to its valley voltage. When the ramp begins to charge back up, the low-side FET turns off and high-side FET turns on. As the PWM ramp voltage exceeds the error amplifier output voltage, the PWM comparator resets the latch, thus turning off the high-side FET and turning on the low-side FET. The low-side FET remains on until the next oscillator pulse discharges the PWM ramp.

During transient conditions, the error amplifier output could be below the PWM ramp valley voltage or above the PWM peak voltage. If the error amplifier is high, the PWM latch is never reset and the high-side FET remains on until the oscillator pulse signals the control logic to turn the high-side FET off and the low-side FET on. The device operates at its maximum duty cycle until the output voltage rises to the regulation set-point, setting VSENSE to approximately the same voltage as REFIN. If the error amplifier output is low, the PWM latch is continually reset and the high-side FET does not turn on. The low-side FET remains on until the VSENSE voltage decreases to a range that allows the PWM comparator to change states. The TPS54672 is capable of sinking current continuously until the output reaches the regulation set-point.



If the current limit comparator trips for longer than 100 ns, the PWM latch resets before the PWM ramp exceeds the error amplifier output. The high-side FET turns off and low-side FET on to decrease the output current. This process is repeated each cycle in which the current limit comparator is tripped.

Dead-Time Control and MOSFET Drivers

Adaptive dead-time control prevents shoot-through current from flowing in both N-channel power MOSFETs during the switching transitions by actively controlling the turnon times of the MOSFET drivers. The high-side driver does not turn on until the gate drive voltage to the low-side FET is below 2 V, while the low-side driver does not turn on until the voltage at the junction of the power MOSFETs (PH pin) is below 2 V.

The high-side and low-side drivers are designed with 300-mA source and sink capability to quickly drive the power MOSFETs gates. The low-side driver is supplied from VIN, while the high-side drive is supplied from the BOOT pin. A bootstrap circuit uses an external BOOT capacitor and internal 2.5- Ω bootstrap switch connected between the VIN and BOOT pins. The bootstrap switch is turned on when the low-side FET is on to charge the BOOT capacitor. The low resistance of the bootstrap switch improves drive efficiency and reduces external component count.

Overcurrent Protection

The cycle by cycle current limiting is achieved using a

sense-FET on the high-side MOSFET and differential amplifier with preset overcurrent threshold. The high-side MOSFET is turned off within 200 ns of the voltage on the sense-FET exceeding the current limit threshold. A 100-ns leading edge blanking circuit prevents false tripping of the current limit when the high-side switch is turning on. Current limit detection occurs only when current flows from VIN to PH when current is being sourced to the output filter. Load protection during current sink operation is provided by thermal shutdown.

Thermal Shutdown

Thermal shutdown turns off the power MOSFETs and disables the control circuits if the junction temperature exceeds the 150°C. The device is released from shutdown automatically when the junction temperature decreases to 10°C, and starts up under control of the slow-start circuit.

Status (STATUS)

The status pin is an open drain output that indicates when internal conditions are sufficient for proper operation. STATUS can be coupled back to a system controller or monitor circuit to indicate that the termination or tracking regulator is ready for start up. STATUS is high impedance when the TPS54672 is operating or ready to be enabled.

STATUS is active low if any of the following occur:

- VIN < UVLO threshold
- VBIAS or internal reference have not settled.
- Thermal shutdown is active.





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PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | | Lead/Ball Finish | | Op Temp (°C) | Top-Side Markings | Samples |
|------------------|--------|--------------|--------------------|------|----------------|----------------------------|------------------|---------------------|--------------|-------------------|---------|
| | (1) | | Drawing | | Qty | (2) | | (3) | | (4) | |
| TPS54672PWP | ACTIVE | HTSSOP | PWP | 28 | 50 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | TPS54672 | Samples |
| TPS54672PWPG4 | ACTIVE | HTSSOP | PWP | 28 | 50 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | TPS54672 | Samples |
| TPS54672PWPR | ACTIVE | HTSSOP | PWP | 28 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | TPS54672 | Samples |
| TPS54672PWPRG4 | ACTIVE | HTSSOP | PWP | 28 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | TPS54672 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.





11-Apr-2013

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





| Α0 | Dimension designed to accommodate the component width |
|----|---|
| | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TPS54672PWPR | HTSSOP | PWP | 28 | 2000 | 330.0 | 16.4 | 6.9 | 10.2 | 1.8 | 12.0 | 16.0 | Q1 |

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*All dimensions are nominal

| Device | Package Type | Package Type Package Drawing | | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|------------------------------|----|------|-------------|------------|-------------|
| TPS54672PWPR | HTSSOP | PWP | 28 | 2000 | 350.0 | 350.0 | 43.0 |

4.4 x 9.7, 0.65 mm pitch

SMALL OUTLINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224765/A



PWP (R-PDSO-G28)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com www.ti.com.

 E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



4206332-34/AO 01/16

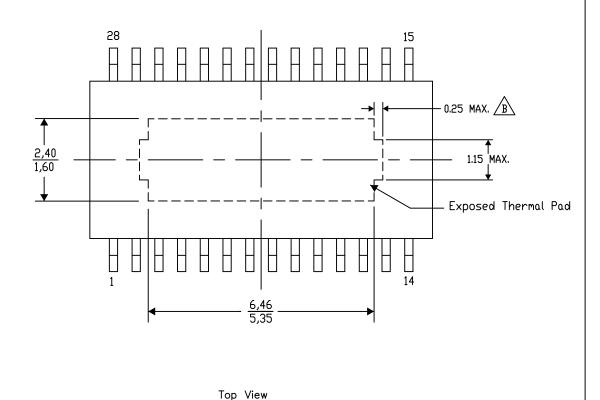
PWP (R-PDSO-G28) PowerPAD™ SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPADTM package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: A. All linear dimensions are in millimeters

B. Exposed tie strap features may not be present.

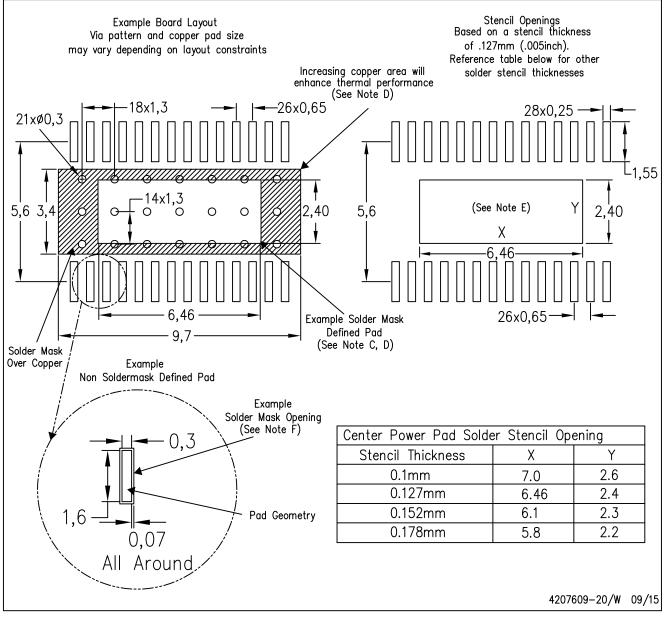
PowerPAD is a trademark of Texas Instruments



Exposed Thermal Pad Dimensions

PWP (R-PDSO-G28)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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